



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} -60 V
- I_D -100 A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) 8.8m Ω
- $R_{DS(ON)}$ (at $V_{GS}=-6V$) 10m Ω
- 100% EAS Tested1
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YJB100GP06H

■ **Electrical Characteristics** ($T_J=25$ unless otherwise noted)

Parameter	Symbol		Min	Typ	Max
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YJB100GP06H

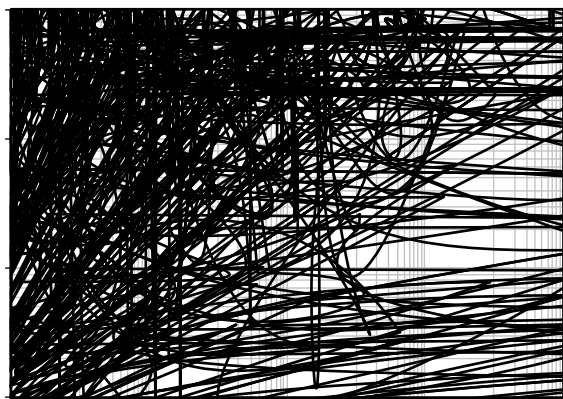
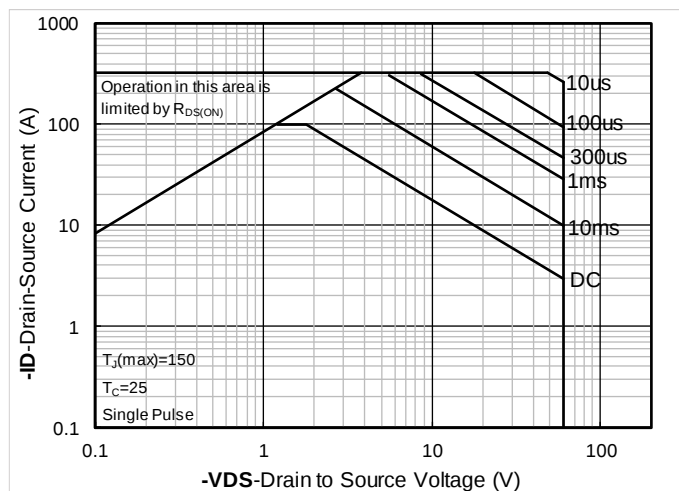


Figure 13. Maximum Transient Thermal Impedance



Figure



■TO-263-HY Package information

SYM.	MIN.	
A2		
b2	0.050	
c		
c2		
D2		
E		
E1		



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